

Amendments to the Claims

This listing of claims replaces all prior versions and listings of claims in the application.

Listing of Claims

1-7. (Canceled)

8. (Withdrawn) A semiconductor device comprising a plurality of TFTs, each of TFTs comprising:

- a semiconductor layer formed on an insulating surface;
  - an insulating film formed on the semiconductor layer; and
  - a gate electrode formed on the insulating film, the gate electrode having a three-layer laminate structure,
- wherein said plurality of TFTs have the same conductivity type.

9. (Withdrawn) A device according to claim 8, wherein the gate electrode comprises a material film containing mainly TaN, a material film containing mainly Al, and a material film containing mainly Ti.

10. (Withdrawn) A device according to claim 8, wherein the gate electrode comprises a material film containing mainly W, a material film containing mainly Al, and a material film containing mainly Ti.

11. (Withdrawn) A device according to claim 8, wherein said plurality of TFTs are n-channel TFTs.

12. (Withdrawn) A device according to claim 8, wherein said plurality of TFTs are p-channel TFTs.

13. (Withdrawn) A device according to claim 8, wherein TFTs formed in a driving circuit of the semiconductor device compose one of an EEMOS circuit and an EDMOS circuit.

14. (Withdrawn) A device according to claim 8, wherein the semiconductor device is a liquid crystal module of one of a transmission type and a reflection type.

15. (Withdrawn) A device according to claim 8, wherein the semiconductor device is a light emitting device having an OLED.

16. (Withdrawn) A device according to claim 8, wherein the semiconductor device is one selected from the group consisting of a video camera, a digital camera, a car navigation system, a personal computer, a portable information terminal, and an electronic game device.

17. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

- forming a semiconductor layer on an insulating surface;
- forming a first insulating film on the semiconductor layer;
- forming a gate electrode, a source wiring of a pixel portion, and an electrode of a terminal portion on the first insulating film by laminating a material film containing mainly TaN, a material film containing mainly Al, and a material film containing mainly Ti and then etching using masks;

- adding an impurity element for providing an n-type to the semiconductor layer using the gate electrode as a mask to form an n-type impurity region;

- etching the gate electrode to form a taper portion;
- forming a second insulating film which covers the source wiring of the pixel portion and the terminal portion; and

- forming a gate wiring and a source wiring of the driver circuit on the second insulating film.

18-19. (Canceled)

20. (Original) A method according to claim 17, wherein the semiconductor device is a light emitting device having an OLED.

21. (Original) A method according to claim 17, wherein the semiconductor device is one selected from the group consisting of a video camera, a digital camera, a car navigation system, a personal computer, a portable information terminal, and an electronic game device.

22. (New) A method of manufacturing a semiconductor device comprising the steps of:  
forming a semiconductor layer on an insulating surface;  
forming a first insulating film on the semiconductor layer;  
forming a gate electrode, a source wiring of a pixel portion, and an electrode of a terminal portion on the first insulating film by laminating a material film containing mainly W, a material film containing mainly Al, and a material film containing mainly Ti and then etching using masks;  
adding an impurity element for providing an n-type to the semiconductor layer using the gate electrode as a mask to form an n-type impurity region;  
etching the gate electrode to form a taper portion;  
forming a second insulating film which covers the source wiring of the pixel portion and the terminal portion; and  
forming a gate wiring and a source wiring of the driver circuit on the second insulating film.

23. (New) A method according to claim 22, wherein the semiconductor device is a light emitting device having an OLED.

24. (New) A method according to claim 22, wherein the semiconductor device is one selected from the group consisting of a video camera, a digital camera, a car navigation system, a personal computer, a portable information terminal, and an electronic game device.